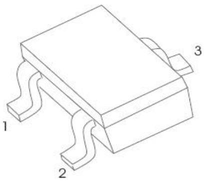
Plastic-Encapsulate Diodes

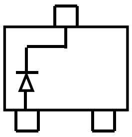
SCHOTTKY BARRIER DIODE

SOT-523

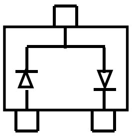


FEATURES

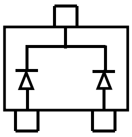
- Low Turn-on Voltage
- Fast Switching



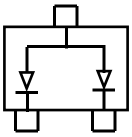
BAS70T Marking: 7C



BAS70-04T Marking: 7D

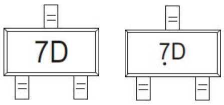
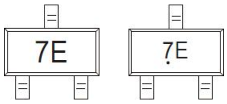
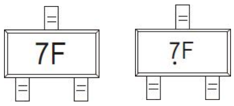


BAS70-05T Marking: 7E



BAS70-06T Marking: 7F

MARKING:

BAS70T	BAS70-04T	BAS70-05T	BAS70-06T
			

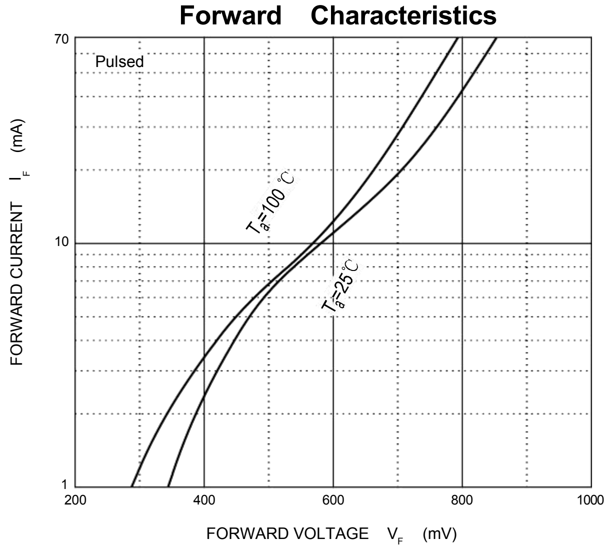
Maximum Ratings @Ta=25℃

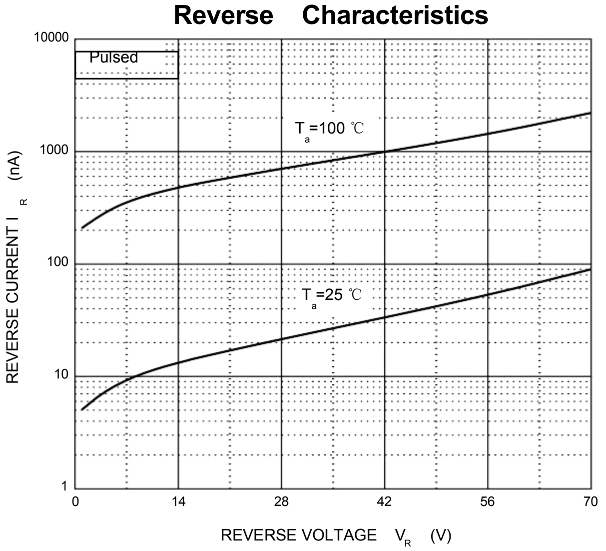
Parameter	Symbol	Limit	Unit
Peak Repetitive Peak Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	70	V
Forward Continuous Current	I_{FM}	70	mA
Non-Repetitive Peak Forward Surge Current @ t = 8.3ms	I_{FSM}	100	mA
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	667	℃/W
Junction temperature	T_J	125	℃
Storage Temperature	T_{STG}	-55~+150	℃

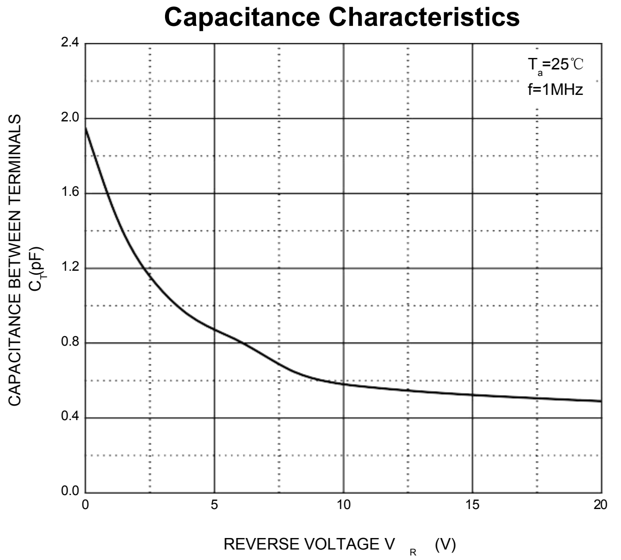
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

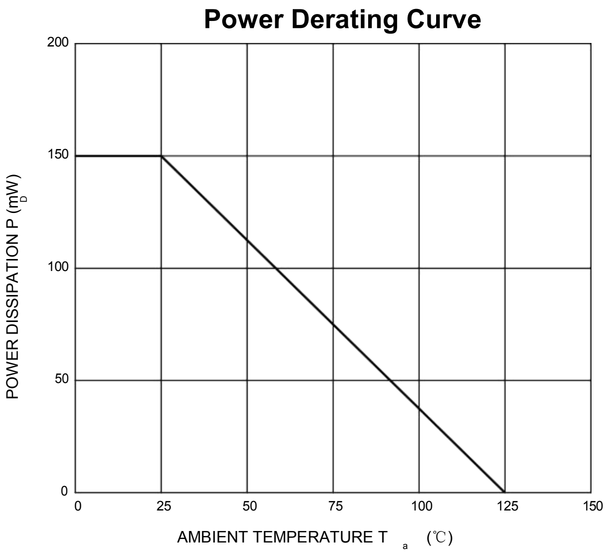
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R=10μA	70		V
Reverse voltage leakag e current	I_R	V_R=50V		100	nA
Forward voltage	V_F	I_F=1mA I_F=15mA		410 1000	mV
Diode capacitance	C_D	V_R=0, f=1MHz		2	pF
Reveres recovery time	t_{rr}	I_F=I_R=10mA,I_{rr}=0.1xI_R, R_L=100Ω		5	ns

Typical Characteristics


Forward Characteristics


Reverse Characteristics


Capacitance Characteristics


Power Derating Curve